The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. – 10. (Canceled)

11. (Currently Amended) A method for manufacturing an organic light emitting diode device ~~hermetically sealed glass package~~, said method comprising the steps of:

providing a first glass plate;

providing a second glass plate;

~~depositing~~ positioning a frit made from glass doped with at least one transition metal and a coefficient of thermal expansion (CTE) lowering filler ~~onto~~ between said first and second glass plates, said filler comprising no more than about 30% of said frit and wherein a mean particle size of said frit is less than or equal to about 20 μm;

positioning an organic light emitting diode between said first and second glass plates; and

heating said frit with ~~an irradiation source~~ a laser in a manner that would cause said frit to soften and form a hermetic seal between said first and second glass plates, thereby hermetically sealing said organic light emitting diode between said ~~which connects said~~ first ~~glass plate to~~ and ~~said~~ second glass plates.

12. (Original) The method of Claim 11, further comprising the step of placing an adhesive within a gap located between outer edges of said first and second glass plates, wherein said gap is caused by the presence of the hermetic seal.

13. – 17. (Canceled)

18. (Currently Amended) The method of Claim 11, wherein a T_g of said frit ~~has a softening temperature that is lower than softening temperatures of said first and second glass plates~~ is less than about 350°C.

19. – 20. (Canceled)

21. (Previously Presented) The method of Claim 11, wherein said CTE lowering filler is an additive filler including lithium alumino-silicate compounds.

22. (Currently Amended) The method of Claim 11, wherein said frit ~~is a low temperature glass frit containing one or more absorbing ions chosen from the group including iron, copper,~~ comprises vanadium or ~~, and~~ neodymium.

23. (Currently Amended) The method of Claim 11, wherein said frit excluding ~~the~~ said CTE lowering filler has the following composition:

K_2O (0-10 mole %)
Fe_2O_3 (0-20 mole %)
Sb_2O_3 (0-40 mole %)
P_2O_5 (20-40 mole %)
V_2O_5 (30-60 mole %)
TiO_2 (0-20 mole %)
Al_2O_3 (0-5 mole %)
B_2O_3 (0-5 mole %)
WO_3 (0-5 mole %)
Bi_2O_3 (0-5 mole %).

24. (Currently Amended) The method of Claim 11, wherein said frit excluding ~~the~~ said CTE lowering filler has the following composition:

K_2O (0-10 mole %)
Fe_2O_3 (0-20 mole %)
Sb_2O_3 (0-20 mole %)
ZnO (0-20 mole %)
P_2O_5 (20-40 mole %)
V_2O_5 (30-60 mole %)
TiO_2 (0-20 mole %)

Al_2O_3 (0-5 mole %)
B_2O_3 (0-5 mole %)
WO_3 (0-5 mole %)
Bi_2O_3 (0-5 mole %).

25. (Previously Presented) The method of Claim 11, wherein said frit is selected from the group of glasses consisting of a titano-vanadium glass, an iron-vanadium glass, a zinc-vanadium glass, a Sn-Zn-phosphate glass, a mixed alkali zinc-phosphate glass, a vanadium-phosphate glass, a Pb-borate glass, and a mixed alkali zinc-phosphate glass with vanadium and lead.

26. – 36. Canceled

37. (Currently Amended) A method for manufacturing an organic light emitting diode device, said method comprising the steps of:

providing a first substrate plate;

providing a second substrate plate;

~~depositing~~ positioning a frit made from a lead-free glass comprising ~~doped with at least one transition metal~~ vanadium and a coefficient of thermal expansion (CTE) lowering filler ~~onto one of~~ between said first and second substrate plates, said frit having a T_g less than about 350°C; and

~~depositing~~ positioning ~~at least one~~ an organic light emitting diode between ~~onto one of~~ said first and second substrate plates; and

heating said frit with a laser ~~an irradiation source and then cooling said frit~~ in a manner that would cause said frit to melt and ~~form a seal which connects~~ bond to said first and second substrate plates ~~to said second substrate plate~~, thereby forming a hermetic seal between said first and second substrate plates, and ~~also protects~~ wherein a temperature of said ~~at least one~~ organic light emitting diode does not exceed about 100°C during said heating.

38. – 46. (Canceled)

47. (Previously Presented) The method of Claim 37, wherein said CTE lowering filler is an inversion filler or an additive filler.

48. – 67. Canceled

68. (New) The method according to claim 11, wherein a mean particle size of said frit is between about 15 μm and 20 μm.

69. (New) The method of claim 11, wherein a mean particle size of said frit is between about 5 μm and about 10 μm.

70. (New) The method of claim 11, wherein said frit was deposited by screen printing.

71. (New) The method of claim 11, wherein a maximum temperature of said organic light emitting diode during said heating is less than about 100°C.

72. (New) The method of claim 11 wherein a maximum temperature of said organic light emitting diode during said heating is less than about 80°C.

73. (New) The method of claim 11 wherein said frit is lead free.

74. (New) The method of claim 11 wherein said filler comprises between about 20% and about 30% of said frit.

75. (New) An organic light emitting diode device made by the process of claim 11.

76. (New) The method of claim 37 wherein a thickness variation of said frit prior to said heating is less than about 10 μm.

77. (New) The method of claim 37 wherein a thickness variation of said frit prior to said heating is less than about 5 μm.

78. (New) The method of claim 37 wherein a mean particle size of said frit is less than or equal to about 20 μm.

79. (New) The method of claim 37 wherein a mean particle size of said frit is between about 15 μm and about 20 μm.

80. (New) The method of claim 37 wherein a mean particle size of said frit is between about 5 μm and 10 μm.

81. (New) A method for manufacturing a hermetically sealed glass package, said method comprising the steps of:

providing a first glass plate;

providing a second glass plate;

positioning a frit made from glass doped with at least one transition metal and a coefficient of thermal expansion (CTE) lowering filler between said first glass plate and said second glass plate, said filler comprising no more than about 30% of said frit and wherein a mean particle size of said frit is less than or equal to about 20 μm;

positioning a temperature sensitive material between said first and second glass plates; and

heating said frit with a laser in a manner that would cause said frit to soften and form a hermetic seal between said first and second glass plates, thereby hermetically sealing said temperature sensitive material between said first and second glass plates and wherein a temperature of said temperature sensitive material does not exceed about 100°C during said heating.

82. (New) The method of claim 81 wherein said temperature sensitive material is an organic material.